

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

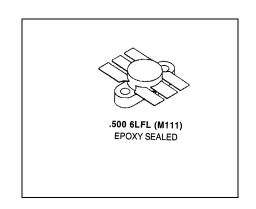
PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1503

RF & MICROWAVE TRANSISTORS WIDE BAND VHF/UHF APPLICATIONS

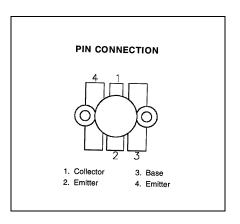
Features

- 400 MHz
- 28 VOLTS
- GOLD METALIZATION
- P_{OUT} = 100 WATTS
- G_P = 7.0 dB GAIN MINIMUM
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1503 is a 28V Class C epitaxial silicon NPN planar transistor designed primarily for UHF communications. The device utilizes diffused emitter resistors to achieve infinite VSWR capability under operating conditions. Internal inpedance matching produces optimum power gain and efficiency over the 225-400MHz band.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	33	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	4.0	Α
P _{DISS}	Power Dissipation	250	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 +150	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	0.7	°C/W





ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol		Test Conditions		Value	ue	Unit
Syllibol	rest conditions		Min.	Typ.	Max.	Offic
BV _{CBO}	I _C = 100 mA	I _E = 0 V	60	-		V
BV _{CEO}	$I_C = 50 \text{ mA}$	$I_B = 0 \text{ mA}$	33			V
BV _{EBO}	I _E = 20 mA	$I_C = 0 \text{ mA}$	4.0			V
I _{CES}	V _{CB} = 28 V	I _E = 0 mA			25	mA
HFE	V _{CE} = 5 V	I _C = 1 A	20		200	

DYNAMIC

Symbol		Test Conditions			Value		Unit	
Symbol	rest Conditions		Min.	Typ.	Max.	Offic		
P _{out}	f = 400 MHz	$P_{IN} = 20W$	$V_{CE} = 28V$	100			w	
G _P	f = 400 MHz	$P_{IN} = 20W$	$V_{CE} = 28V$	7.0			dB	
ης	f = 400 MHz	$P_{IN} = 20W$	$V_{CE} = 28V$	50			%	
Cob	f =1 MHz	$V_{CB} = 28V$				105	pf	

IMPEDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{\mathtt{CL}}(\Omega)$
225 MHz	1.3 + j1.8	5.4 – j0.5
300 MHz	1.1 + j2.4	3.9 – j0.7
350 MHz	0.8 + j3.0	2.6 – j1.0
375 MHz	0.75 + j3.5	2.2 – j1.4
400 MHz	0.70 + j3.6	1.8 – j1.9

P_{IN} = 20 W V_{CE} = 28 V





PACKAGE MECHANICAL DATA

